Amendments to the Specification

Please replace the paragraph [0059] with the following amended paragraph:

[0059] Fig. 3D shows a corresponding layout of a second mask used by the third lithography process. If a positive resist is used for the third lithography process, large features 310 in Fig. 3D with widths W4 and W5 of the second mask are ~~oblique~~ opaque features on a transparent mask 340. Tonality of mask and features are reversed if a negative resist is used for the third lithography process.